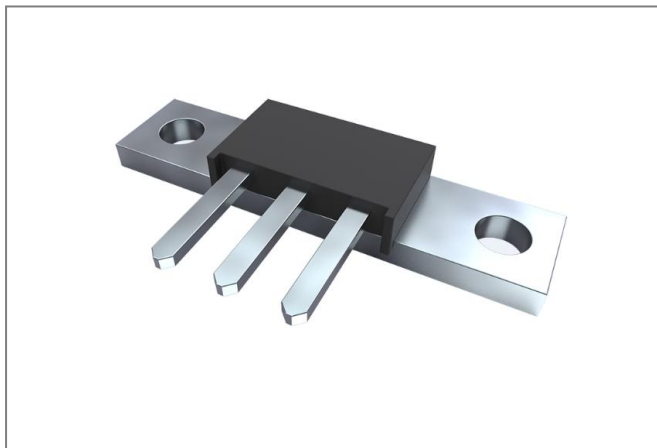


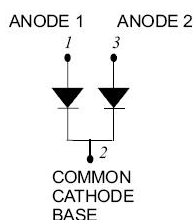
## 81CNQ045S2 SCHOTTKY RECTIFIER



### Features

- 175°C T<sub>J</sub> operation
- Center tap module
- Very Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Low profile, high current package
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional electrical and life testing can be performed upon request

### Circuit Diagram



### Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

### Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	-	45	V
Average Rectified Forward Current	I <sub>F (AV)</sub>	50% duty cycle @T <sub>C</sub> =141°C, rectangular wave form	40(Per Leg) 80(Per Device)	A
Peak One Cycle Non-Repetitive Surge Current(Per leg)	I <sub>FSM</sub>	8.3 ms, half Sine pulse	950	A
Non-Repetitive Avalanche Energy (Peg leg)	E <sub>AS</sub>	T <sub>J</sub> =25°C, I <sub>AS</sub> =8A, L=1.7mH	54	mJ
Repetitive Avalanche Current(Peg leg)	I <sub>AR</sub>	Current decaying linearly to zero in 1 µsec Frequency limited by T <sub>J</sub> max. V <sub>A</sub> =1.5×V <sub>R</sub> typical	8	A

**Electrical Characteristics:**

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop (Per leg) *	V <sub>F1</sub>	@ 40A, Pulse, T <sub>J</sub> = 25 °C @ 80A, Pulse, T <sub>J</sub> = 25 °C	0.54 0.64	0.60 0.74	V
	V <sub>F2</sub>	@ 40A, Pulse, T <sub>J</sub> = 125 °C @ 80A, Pulse, T <sub>J</sub> = 125 °C	0.46 0.56	0.54 0.66	V
Reverse Current (Per leg) *	I <sub>R1</sub>	@V <sub>R</sub> = rated V <sub>R</sub> T <sub>J</sub> = 25 °C	0.03	5	mA
	I <sub>R2</sub>	@V <sub>R</sub> = rated V <sub>R</sub> T <sub>J</sub> = 125 °C	25	45	mA
Junction Capacitance (Per leg)	C <sub>T</sub>	@V <sub>R</sub> = 5V, T <sub>C</sub> = 25 °C f <sub>SIG</sub> = 1MHz	2200	2600	pF

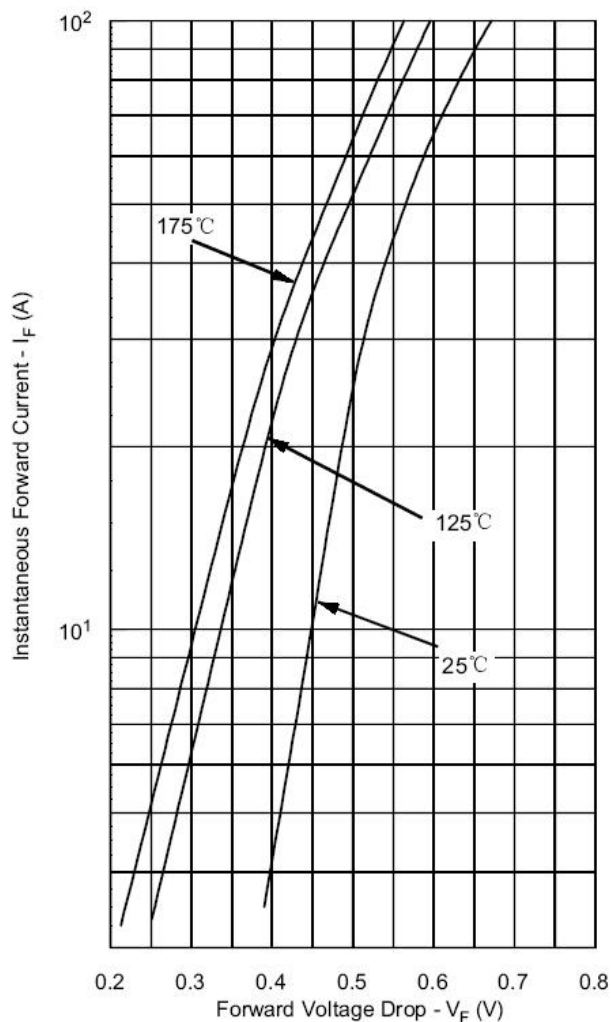
\* Pulse width < 300 μs, duty cycle < 2%

**Thermal-Mechanical Specifications:**

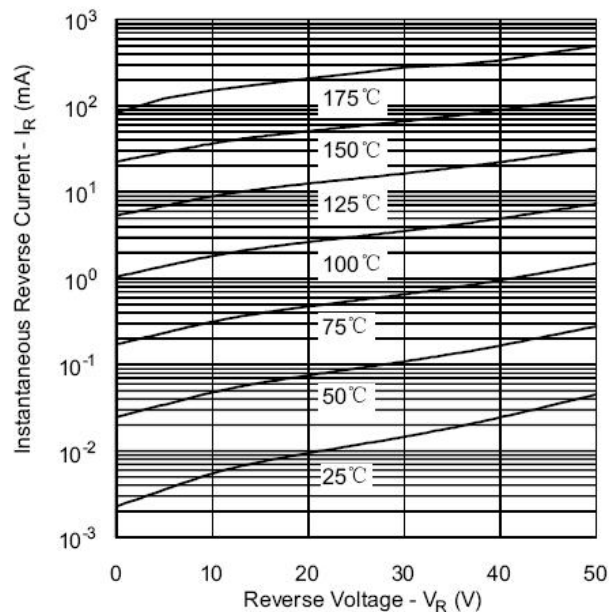
Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T <sub>J</sub>	-	-55 to +175	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +175	°C
Typical Thermal Resistance Junction to Case (per leg)	R <sub>θJC</sub>	DC operation	0.85	°C/W
Typical Thermal Resistance Junction to Case (per package)	R <sub>θJC</sub>	DC operation	0.42	°C/W
Typical Thermal Resistance, case to Heat Sink	R <sub>θcs</sub>	Mounting surface, smooth and greased	0.30	°C/W
Mounting Torque	TM	-	40(min)	Kg-cm
			58(max)	
Approximate Weight	wt	-	7.8	g
Case Style	PRM2			

## Ratings and Characteristics Curves

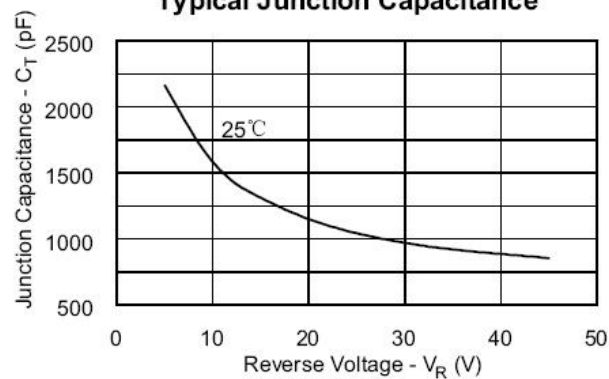
**Typical Forward Characteristics**



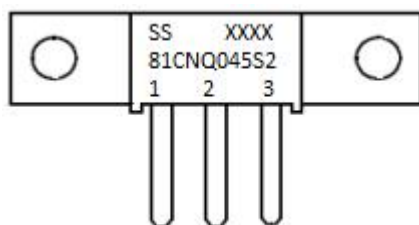
**Typical Reverse Characteristics**



**Typical Junction Capacitance**



## Marking Diagram



Where XXXX is YYWW

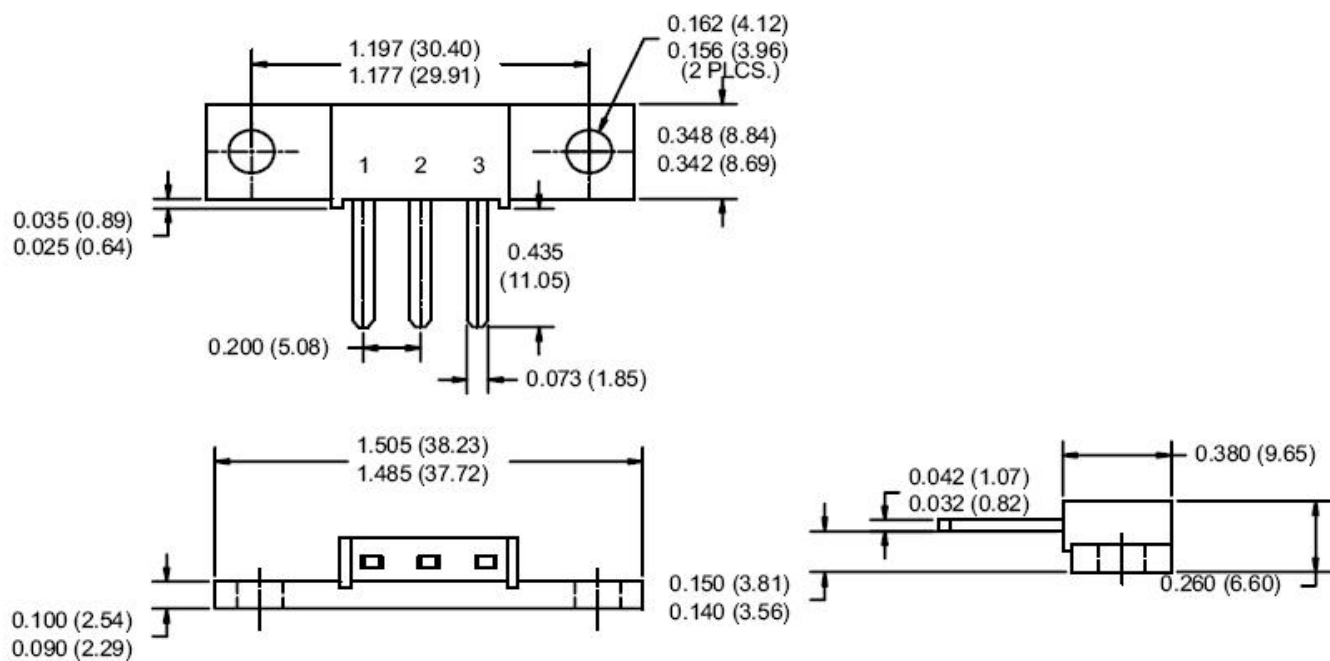
1st row SS YYWWL  
2nd row 81CNQ045S2  
3rd row 1 2 3 (pin)  
SS = SS  
YY = Year  
WW = Week

**Cautions:** Molding resin  
Epoxy resin UL:94V-0

## Ordering Information

Device	Package	Terminals finish	Baseplate finish	Shipping
81CNQ045S2	PRM2	Pure Sn dipped (dipped height 6-8mm)	Nickel plated	48pcs / box

## Mechanical Dimensions PRM2 (Inches/Millimeters)



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